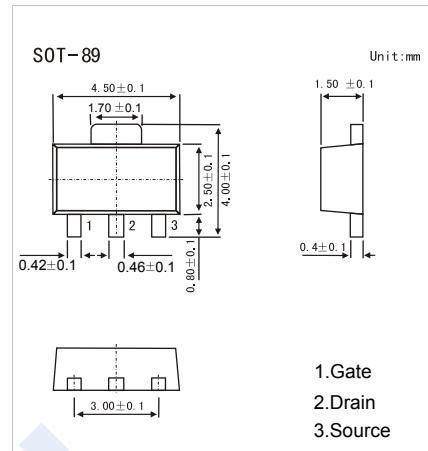
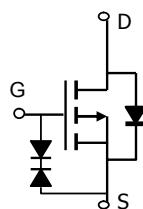


P-Channel MOSFET

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■ Features

- $V_{DS} (V) = -60V$
- $I_D = -1 A$
- $R_{DS(ON)} < 0.73 \Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 1.2 \Omega$ ($V_{GS} = -4V$)
- High forward transfer admittance

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Drain-Gate voltage ($R_{GS} = 20 k\Omega$)	V_{DG}	-60	
Gate-Source Voltage	V_{GS}	± 20	A
Continuous Drain Current	I_D	-1	
Pulsed Drain Current	I_{DM}	-4	W
Power Dissipation	P_D	0.5	
		1.5	
Thermal Resistance, Channel to Ambient	R_{QJA}	250	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-10mA, V _{GS} =0V	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DSS} =-60V, V _{GS} =0V			-100	uA
Gate-Body leakage current	I _{GSS}	V _{DSS} =0V, V _{GS} =±16V			±10	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DSS} =-10V, I _D =-1mA	-0.8		-2	V
Static Drain-Source On-Resistance	R _{D(on)}	V _{GS} =-4V, I _D =-0.5A			1.2	Ω
		V _{GS} =-10V, I _D =-0.5A			0.73	
		V _{GS} =-4V, I _D =-0.5A				
Forward Transconductance	g _{FS}	V _{DSS} =-10V, I _D =-0.5A	0.5	1		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DSS} =-10V, f=1MHz		155		pF
Output Capacitance	C _{oss}			22		
Reverse Transfer Capacitance	C _{rss}			75		
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DSS} =-48V, I _D =-1A		6.5		nC
Gate Source Charge	Q _{gs}			4.5		
Gate Drain Charge	Q _{gd}			2		
Turn-On DelayTime	t _{d(on)}	 Duty ≤ 1%, t _w ≥ 10μs		20		ns
Turn-On Rise Time	t _r			17		
Turn-Off DelayTime	t _{d(off)}			100		
Turn-Off Fall Time	t _f			20		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-1A, V _{GS} =0, dI/dt=50A/μs		50		nC
Body Diode Reverse Recovery Charge	Q _{rr}			45		
Continuous drain reverse current	I _{DR}				-1	A
Pulse drain reverse current	I _{DRP}				-4	
Diode Forward Voltage	V _{SD}	I _{DR} =-1A, V _{GS} =0V			-1.8	V

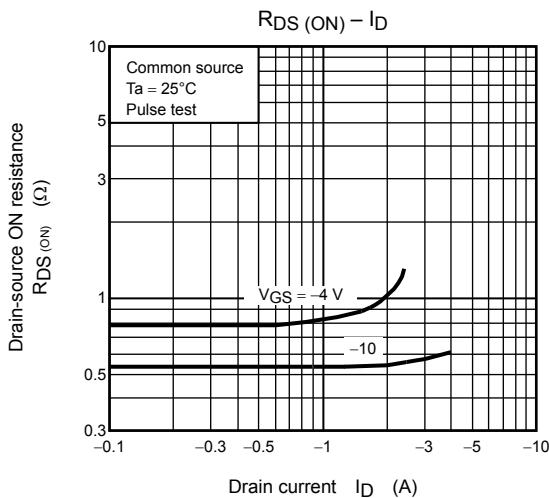
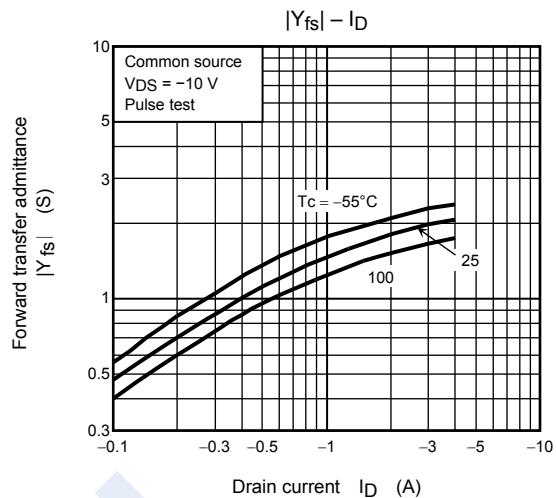
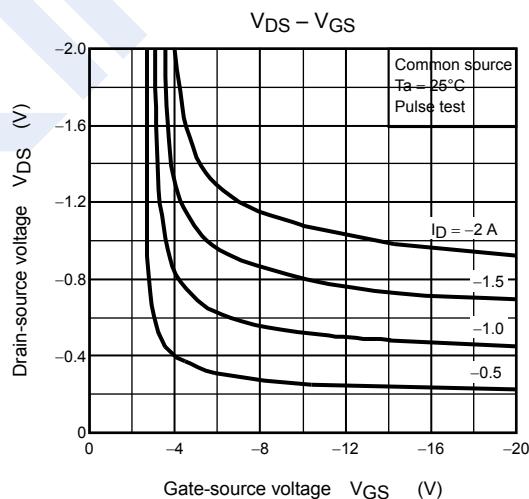
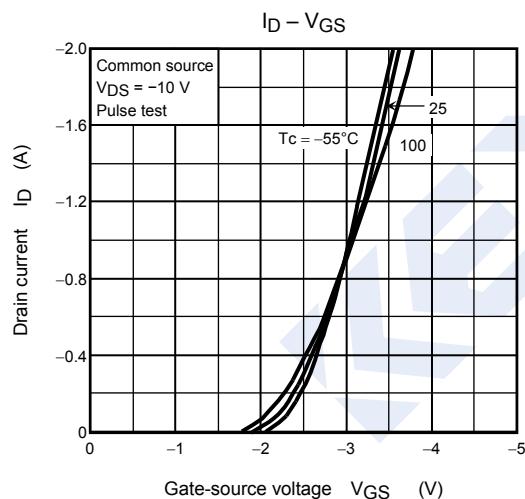
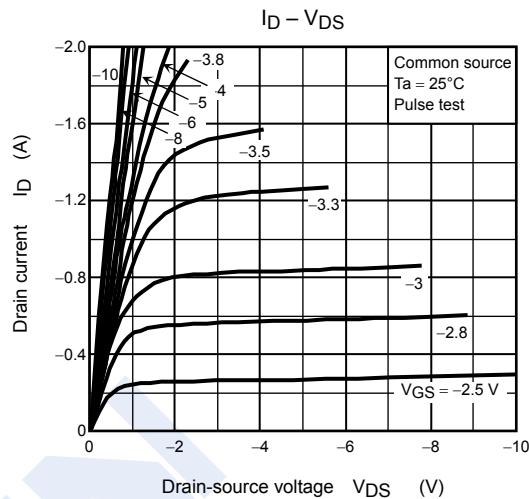
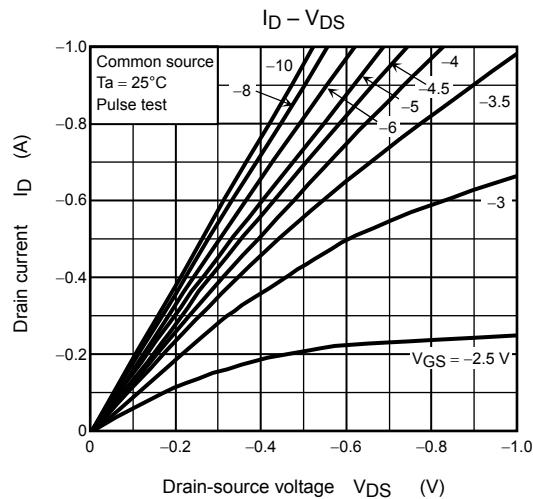
■ Marking

Marking	Z*8
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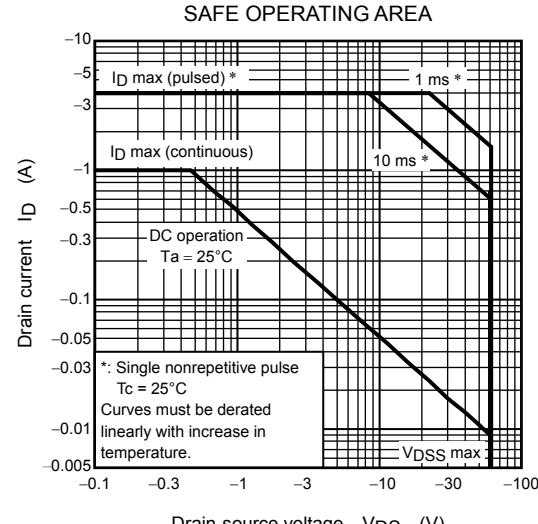
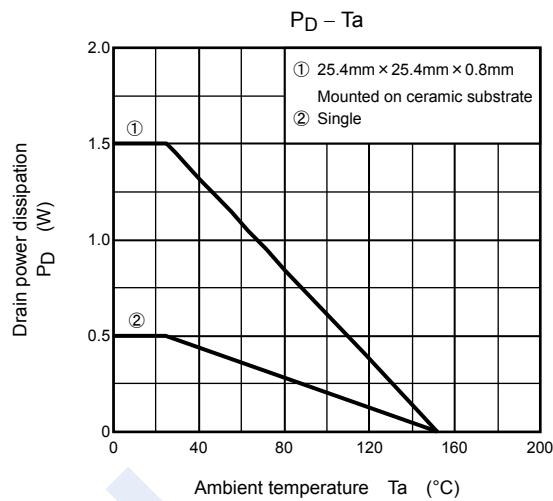
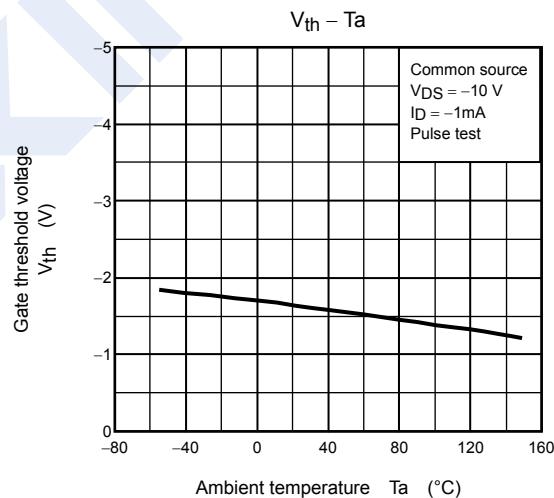
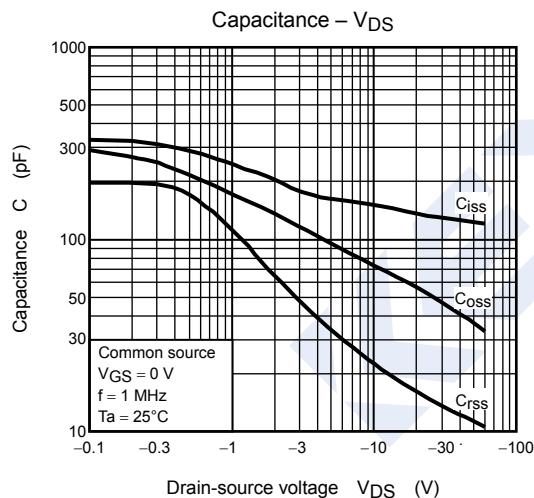
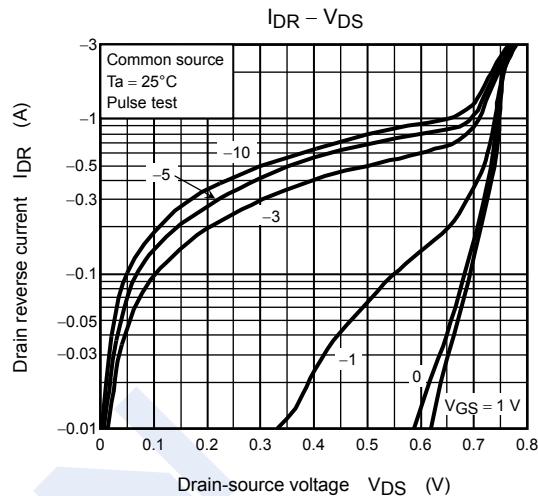
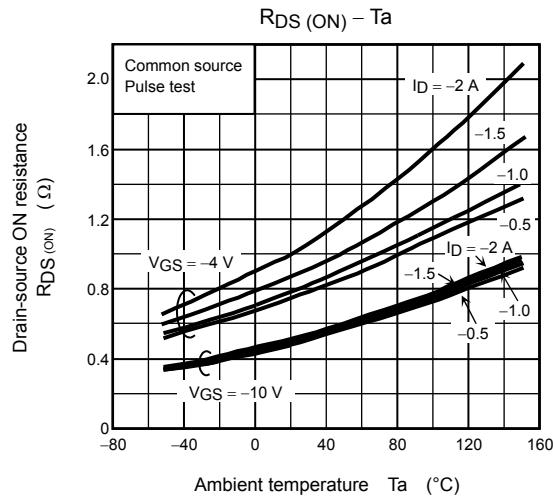
■ Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics



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■ Typical Characteristics

